## NSN 5961-01-365-6420

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View Online at https://aerobasegroup.com/nsn/5961-01-365-6420 **Inclosure Material:** Metal **Overall Length:** 1.290 inches **Overall Diameter:** 0.597 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.667 inches Thready Qty Per Inch (tpi): 28 **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 3.0 gate trigger voltage, dc and 3.0 on-state voltage, peak **Current Rating Per Characteristic:** 250.00 milliamperes drain current peak **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: npnp **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 uninsulated wire lead w/terminal lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:** 

No

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